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Sommario/riassunto	Silicon carbide is known to have been investigated since 1907 when

Captain H J Round demonstrated yellow and blue emission by applying bias between a metal needle and an SiC crystal. The potential of using SiC in semiconductor electronics was already recognized half a century ago. Despite its well-known properties, it has taken a few decades to overcome the exceptional technological difficulties of getting silicon carbide material to reach device quality and travel the road from basic research to commercialization. This second of two volumes reviews four important additional areas: the growth